

Dual N-Channel 30 V (D-S) MOSFET with Schottky Diode

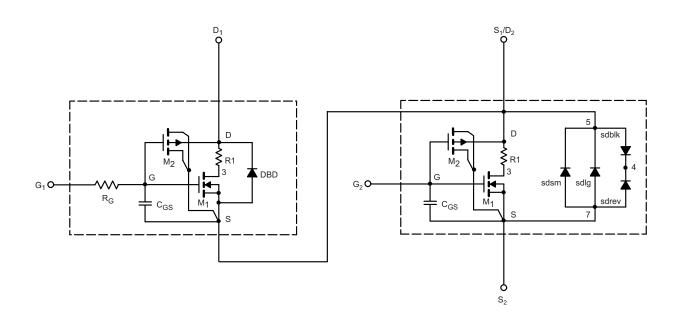
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- · Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS		SIMULATED DATA	MEASURED DATA	UNIT
Static						
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\;\mu\text{A}$	Ch-1	2	-	V
			Ch-2	2	-	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 8 \text{ A}$	Ch-1	0.0162	0.0165	Ω
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 8 \text{ A}$	Ch-2	0.0153	0.0155	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6 \text{ A}$	Ch-1	0.0217	0.0215	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6 \text{ A}$	Ch-2	0.022	0.020	
Forward Transconductance ^a	g fs	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 8 \text{ A}$	Ch-1	25	29	S
		V _{DS} = 15 V, I _D = 8 A	Ch-2	24	33	
Diode Forward Voltage ^b	V _{SD}	$I_{\rm S} = 1.7 \text{ A}, V_{\rm GS} = 0 \text{ V}$	Ch-1	0.78	0.77	V
		$I_{\rm S} = 1 {\rm A}, {\rm V}_{\rm GS} = 0 {\rm V}$	Ch-2	0.45	0.46	
Dynamic ^b						
Total Gate Charge	Qg		Ch-1	6.8	6.7	
		Channel 1	Ch-2	7	7	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$ Channel 2 $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$	Ch-1	2.8	2.2	nC
			Ch-2	2.8	2.8	
Gate-Drain Charge	Q _{gd}		Ch-1	2	2	
			Ch-2	2	2	

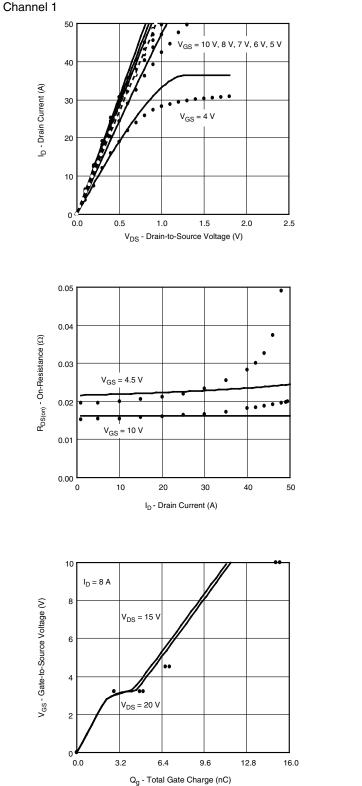
Notes

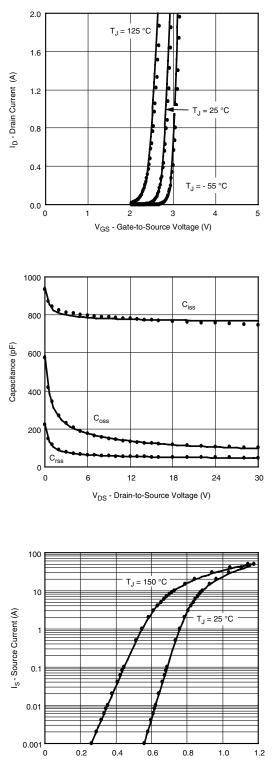
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA T_J = 25 °C, unless otherwise noted





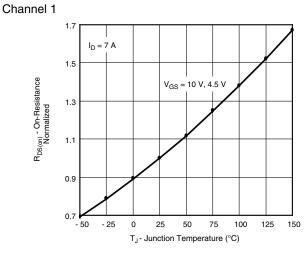
V_{SD} - Source-to-Drain Voltage (V)

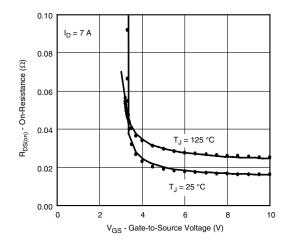
Note

Dots and squares represent measured data.



COMPARISON OF MODEL WITH MEASURED DATA T_J = 25 °C, unless otherwise noted





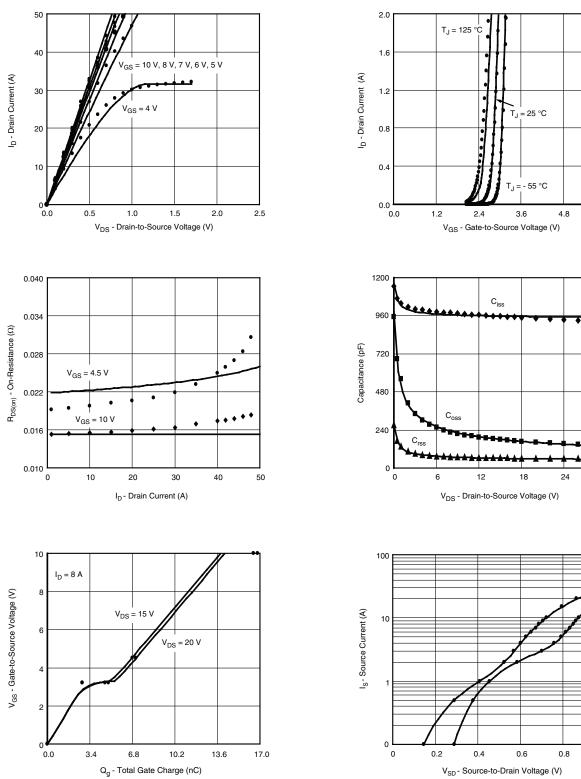


6.0

30

COMPARISON OF MODEL WITH MEASURED DATA T_J = 25 °C, unless otherwise noted

Channel 2

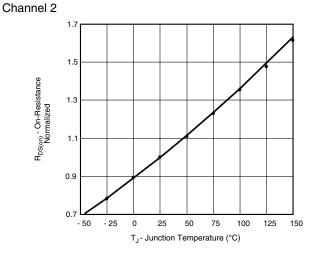


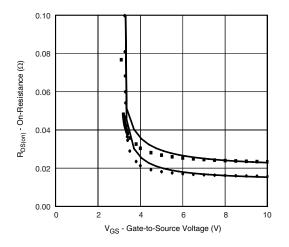
Note Dots and squares represent measured data.

1.0



COMPARISON OF MODEL WITH MEASURED DATA T_J = 25 °C, unless otherwise noted







Vishay

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